

Figure 1.—Theoretically calculated equilibrium curves for systems QT_2 vs. MZ in which two kinds of monofunctional substituents, T and Z, are scrambled between a bifunctional central moiety, Q, and a monofunctional central moiety, M. The calculations correspond to $K_1 = 0.250$ (ideal randomness) and varying K_1 : A, $K_1 = 10^{-20}$; B, $K_1 = 10^{-5}$; C, $K_1 = 1.00$ (ideal randomness); D, $K_1 = 10^{+5}$; E, $K_1 = 10^{+20}$. Curve a corresponds to the concentration of the MZ molecule, b to the MT, c to the QZ₂, d to the QZT, and e to the QT₂ molecule, with the over-all composition being given by the parameter $R \equiv Z/(Q + M)$, $R' \equiv M/(Q + M)$.

methyl groups. Halogens also prefer the silicon moiety bearing the larger number of organic substituents when equilibrated with silanic hydrogen.¹¹

Estimations of the enthalpy of the reaction of eq 1 based on the bond-energy approach² show that the values of ΔH , assuming only σ -bond contributions, differ considerably from ΔH values that were calculated from the intersystem constants $K_{\rm I}$ according to the approximation

(11) D. R. Weyenberg, A. Bey, and P. J. Ellison, J. Organometal. Chem. (Amsterdam), 3, 489 (1965).

 $\Delta H \approx \Delta F = -RT \ln [K_1/(K_1)_{rand}]$

We attribute these differences to π -bonding effects which, therefore, appear to be the major driving force for the nonrandom equilibrations of eq 1. Quantum mechanical calculations¹² support the concept of the major influence of π contributions in these reactions.

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(12) J. H. Letcher and J. R. Van Wazer, in preparation.

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The Mass Spectra of Volatile Hydrides. V. Silylarsine^{1,2}

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The mass spectra of silylarsine, H₂AsSiH₃, arsine, AsH₃, and diarsine, H₂AsAsH₂, have been studied. From appearance potential data, the heat of formation of several silylarsine positive ions and the following thermochemical values have been calculated (in kcal/mole): $\Delta H_{\rm f}^{\circ}({\rm H}_2{\rm AsSiH}_3) = 37$; $D({\rm H}_2{\rm As}-{\rm SiH}_3) = 73$; $I(\cdot{\rm AsH}_2) = 213$; $\Delta H_{\rm f}^{\circ}(\cdot{\rm AsH}_2) = 60$; and $\Delta H_{\rm f}^{\circ}(\cdot{\rm SiH}_2) = 81$.

Introduction

Silylarsine has been prepared by several investigators,^{3,4} and although a mass spectrometer was employed in one of the studies³ for the identification of this hydride, neither the fragmentation pattern nor any appearance potential measurements were reported. It is the purpose of this paper to report these data, the heat of formation of several of the positive ions of silylarsine, the silicon–arsenic bond dissociation energy, and the standard heat of formation of silylarsine.

Experimental Section

Silylarsine was prepared by the method of Drake and Jolly³ in a vacuum system which contained no grease. Equimolar amounts of silane and arsine were circulated by an automatic Toepler pump through a silent electric discharge, operated at 6 kv ac, and a U trap cooled with an ethanol slush (-125°) for 6 hr. At 1-hr intervals, the discharge was stopped, the U trap was cooled with liquid nitrogen, and any volatile substances remaining in the system were quickly removed by evacuation. Silylarsine and tetrasilane, Si₄H₁₀, were separated from the other compounds formed in the discharge reaction by fractional distillation using conventional vacuum techniques.⁶ It was not possible to separate completely silylarsine from tetrasilane by either distillation or with a gas-liquid chromatographic column (12 ft \times 0.25-in. i.d.), packed with 10% Silicone 702 on Celite.

⁽¹⁾ Paper IV: F. E. Saalfeld and H. J. Svec, J. Phys. Chem., 70, 1753 (1966).

⁽²⁾ Presented at the 14th Annual ASTM E-14 Conference on Mass Spectrometry and Allied Topics, Dallas, Texas, May 22-27, 1966.

⁽³⁾ J. E. Drake and W. L. Jolly, Chem. Ind. (London), 1470 (1962).
(4) B. J. Aylett, H. J. Emeléus, and A. G. Maddock, J. Inorg. Nucl.

⁽⁴⁾ B. J. Aylett, H. J. Emeléus, and A. G. Maddock, J. Inorg. Nucl. Chem. 1, 187 (1955).

Several times during the course of this investigation, an explo-

⁽⁵⁾ R. T. Sanderson, "Vacuum Manipulation of Volatile Compounds," John Wiley and Sons, Inc., New York, N. Y., 1948.

sion occurred in the sample bulb. Mass spectral analysis of the volatile compounds remaining in the sample bulb after the explosion showed only the silylarsine had decomposed; the amount of tetrasilane was the same before and after the explosion. Further, none of the constituents of air was observed in the analysis, and the metallic mirror formed on the bulb in the explosion gave a positive spot test for arsenic. It was found that the explosion could be prevented if the samples were shielded from light; thus, all of the sample bulbs were painted black and stored in a light-tight photographic sleeve, and the experiments were conducted in a darkened room. A more intensive investigation of this apparent photolysis reaction of silylarsine is planned.

The data reported here were obtained on a 12-107 Bendix Timeof-Flight mass spectrometer, operated in the pulsed ion mode, which has been modified⁶ for appearance potential measurements. This modification, which takes advantage of the multiple analog output systems of the Bendix instrument, permits the chart drive of a two-pen recorder to be synchronized with the continuously decreasing voltage of the linear electron energy control. A start-stop timer was used to energize simultaneously the chart drive and the electron energy control drive motor. The electron energy control potentiometer was rotated by a synchronous 60-c motor, mechanically coupled to the potentiometer through a gear rack. It was possible to obtain the appearance potential curves for two ions (an ion from the hydride and argon, the internal standard used to calibrate the voltage scale) simultaneously in less than 2 min with this modification. The fragmentation pattern was obtained using 70-v electrons and an ionizing current of 0.125 $\mu a.$

Results and Discussion

Mass spectral data for silvlarsine, arsine, and diarsine are shown in Table I. No mass spectral properties of the SiH_x⁺ (x = 0-3) fragment ions of silvlarsine are reported because the presence of tetrasilane makes the precursor of these ions ambiguous.

In order to calculate the dissociation energy and standard heat of formation for silvlarsine from the data given in Table I, the following ancillary data are required (in kcal/mole): $\Delta H_{f}^{\circ}(\cdot H) = 52.1$; $\Delta H_{f}^{\circ}(AsH_{3})$ 15.9^{*} $\Delta H_{\rm f}^{\rm o}({\rm H}_3{\rm SiSiH}_3) = 17.1;^9$ $\Delta H_{\rm f}^{\circ}({\rm SiH}_4)$ _ 7.3:9 $\Delta H_{f}^{\circ}(H_{2}AsAsH_{2}) = 35.2;^{10} \quad \Delta H_{f}^{\circ}(\cdot SiH_{3})$ -----50.4.11 Although the relative abundances of all = of the arsine ions and the appearance potentials for As⁺ and AsH⁺ agree well with the data previously published,¹² the appearance potentials for AsH₂⁺ and AsH_3^+ in the two studies are in discord. It has been pointed out by Svec¹³ that the appearance potentials for AsH₈⁺ and AsH₂⁺ cited in the earlier work¹² may have been for an excited state. This seems to be the case as the value for the ionization potential of AsH₃ reported here agrees well with the value of 10.6 ev cited by Kiser.14

The relationship between appearance potentials and heats of formation and bond energies is well known, as

(6) R. S. Olfky and F. E. Saalfeld, "Report of NRL Progress," June 1965, p 56.

- (9) S. R. Gunn and L. G. Green, ibid., 65, 779 (1961).
- (10) F. E. Saalfeld and H. J. Svec, Inorg. Chem., 2, 50 (1963).
- (11) F. E. Saalfeld and H. J. Svec, ibid., 3, 1442 (1964). (12) F. E. Saalfeld and H. J. Svec, ibid., 2, 46 (1963).
- (13) H. J. Svec in "Mass Spectrometry," R. I. Reed, Ed., Academic Press Inc., New York, N. Y., 1966, p 245.
- (14) R. W. Kiser, "Introduction to Mass Spectrometry and its Applications," Prentice-Hall, Inc., Englewood Cliffs, N. J., 1965, p 308.

		TABLE I: SU	IMMARY OF RESUI	TS
Postulated ion scurce reaction	Rel abundance	ap, ^{a,b} ev	ap, ^{a,b} kcal/mole	Thermochemistry, ^b kcal/mole
e⁻ ∔ H₂As²8SiH₃ →> As²8SiH₅⁺ + 2e⁻	59.0	$10.1 \pm 0.1^{\circ}$	233	$\Delta H_{\rm f}^{\rm o}({\rm AsSiH_5^+}) = {\rm ap} + \Delta H_{\rm f}^{\rm o}({\rm H_2AsSiH_3}) = 270$
e⁻ ∔ H₂As ³⁸ SiH₃ →> As ²⁸ SiH₄ ⁺ + H + 2e [−]	18.1	11.0 ± 0.3	254	$\Delta H_{\rm f}^{\circ}({\rm AsSiH_4^{+}}) = {\rm ap} + \Delta H_{\rm f}^{\circ}({\rm H_2AsSiH_3}) - \Delta H_{\rm f}^{\circ}(\cdot{\rm H}) = 239$
e [−] + H₂As ³⁸ SiH ₃ → As ²⁸ SiH ₃ ⁺ + H ₂ + 2e [−]	100	9.7 ± 0.1	224	$\Delta H_{\rm f}^{\circ}({\rm AsSiH}_3^+) = {\rm ap} + \Delta H_{\rm f}^{\circ}({\rm H}_2 {\rm AsSiH}_3) - \Delta H_{\rm f}^{\circ}({\rm H}_2) = 261$
e^- + H ₂ As ³⁸ SiH ₃ \longrightarrow As ²⁸ SiH ₂ ⁺ + H ₂ + H + 2 e^-	22.5	13.7 ± 0.2	316	$\Delta H_{f}^{\circ}(\text{AsSiH}_{2}^{+}) = \text{ap} + \Delta H_{f}^{\circ}(\text{H}_{2}\text{AsSiH}_{3}) - \Delta H_{f}^{\circ}(\text{H}_{2}) - \Delta H_{f}^{\circ}(\cdot\text{H}) = 301$
e [−] + H ₂ As ²⁸ SiH ₃ → As ²⁸ SiH ⁺ + 2H ₂ + 2e [−]	90.1	13.4 ± 0.1	309	$\Delta H_{\rm f}^{\circ}(\rm AsSiH^{+}) = ap + \Delta H_{\rm f}^{\circ}(\rm H_2ASSiH_3) - 2\Delta H_{\rm f}^{\circ}(\rm H_2) = 346$
e ⁻ + H ₂ As ²⁸ SiH ₃ → As ²⁸ Si ⁺ + 2H ₂ + H + 2e	41.6	16.8 ± 0.3	387	$\Delta H_{f}^{\circ}(\text{AsSi}^{+}) = \text{ap} + \Delta H_{f}^{\circ}(\text{H}_{2}\text{AsSiH}_{3}) - 2\Delta H_{f}^{\circ}(\text{H}_{2}) - \Delta H_{f}^{\circ}(\cdot \text{H}) = 372$
$e^- + H_2As^{28}SiH_3 \longrightarrow AsH_3^+ + {}^{28}SiH_2 + 2e^-$	0.1	13.1 ± 0.6	302	$\Delta H_{f}^{\circ}(\cdot \operatorname{SiH}_{2}) = \operatorname{ap} + \Delta H_{f}^{\circ}(\operatorname{H}_{2}\operatorname{ASSH}_{3}) - \Delta H_{f}^{\circ}(\operatorname{ASH}_{3}^{+}) = 81$
$e^- + H_2As^{28}SiH_3 \longrightarrow AsH_2^+ + {}^{28}SiH_3 + 2e^-$	42.6	12.4 ± 0.2	286	$\Delta H_{f}^{\circ}(H_{2}ASSiH_{3}) = \Delta H_{f}^{\circ}(ASH_{2}^{+}) + \Delta H_{f}^{\circ}(\cdot SiH_{3}) - ap = 37$
				$D(H_2AS-SiH_3) = ap - I(\cdot ASH_2) = 73$
$e^- + H_2As^{38}SiH_3 \longrightarrow AsH^+ + ? + 2e^-$	42.3	:	:	:
e ⁻ + H ₂ As ³⁸ SiH ₃ → As ⁺ + ? + 2e ⁻	56.1	:	:	:
$e^- + AsH_3 \longrightarrow AsH_3^+ + 2e^-$	70.2	10.5 ± 0.1	242	$\Delta H_{f}^{\sigma}(AsH_{3}^{+}) = ap + \Delta H_{f}^{\sigma}(AsH_{3}) = 258$
e ⁻ + AsH ₃ → AsH ₂ ⁺ + H + 2e ⁻	22.8	13.4 ± 0.2	309	$\Delta H_{\rm f}^{\rm o}({\rm AsH}_3^+) = {\rm ap} + \Delta H_{\rm f}^{\rm o}({\rm AsH}_3) - \Delta H_{\rm f}^{\rm o}(\cdot {\rm H}) = 273$
$e^- + AsH_3 \longrightarrow AsH^+ + H_2 + 2e^-$	100	12.5 ± 0.2	288	$\Delta H_{\rm f}^{\rm o}({\rm AsH^+}) = {\rm ap} + \Delta H_{\rm f}^{\rm o}({\rm AsH_3}) - \Delta H_{\rm f}^{\rm o}({\rm H_2}) = 304$
e^- + AsH ₃ \longrightarrow As ⁺ + H ₂ + H + 2e ⁻	36.5	15.0 ± 0.3	346	$\Delta H_{f}^{\circ}(As^{+}) = ap + \Delta H_{f}^{\circ}(AsH_{3}) - \Delta H_{f}^{\circ}(H_{2}) - \Delta H_{f}^{\circ}(\cdot H) = 310$
e ⁻ + AsH ₃ → AsH ₃ ²⁺ + 3e ⁻	0.04	:	:	
$e^- + AsH_3 \longrightarrow AsH_2^{2+} + H + 3e^-$	0.3	:	:	:
$e^- + AsH_3 \longrightarrow AsH^{2+} + H_2 + 3e^-$	2.2		:	
$e^- + AsH_3 \longrightarrow As^{2+} + H_2 + H + 3e^-$	1.5	:	•	:
e [−] + H ₂ AsAsH ₆ → AsH ₂ ⁺ + AsH ₂ + 2e [−]	::	12.9 ± 0.4	298	$\Delta H_{\rm f}^{\rm o}(\cdot {\rm AsH_2}) = {\rm ap} + \Delta H_{\rm f}^{\rm o}({\rm H_2AsAsH_2}) - \Delta H_{\rm f}^{\rm o}({\rm AsH_2^+}) = 60$
			$I(\cdot AsH_2) =$	$\Delta H_{\rm f}^{\circ}({\rm AsH_2^+}) - \Delta H_{\rm f}^{\circ}(\cdot {\rm AsH_2}) = 213; D({\rm H_2As-AsH_2}) = {\rm ap} - I(\cdot {\rm AsH_2}) = 85$
^a Average of at least seven independent measureme	nts determined by V	Varren's method o	f extrapolated di	ferences: J. W. Warren, Nature, 165, 811 (1950). ^b ap = appearance potential;
ΔH_{f}° = standard heat of formation; I = ionization p	otential; $D = disso$	ciation energy; 1	$ev = \overline{23.06 \text{ kcal}}$	mole. ° Standard deviation.

⁽⁷⁾ T. L. Cottrell, "The Strengths of Chemical Bonds," 2nd ed, Butterworth and Co. Ltd., London, 1958, p 153.

⁽⁸⁾ S. R. Gunn, W. L. Jolly, and L. G. Green, J. Phys. Chem., 64, 1334 (1960).

are the errors in this type of measurement.^{12, 15} In using the data presented in Table I to calculate the heat of formation and bond dissociation, it has been assumed that the measured appearance potentials do not include excess kinetic or excitation energy. Since this assumption could not be tested experimentally, values cited here should be taken as a lower limit for the heat of formation and an upper limit for the bond dissociation energy. These values are 37 and 73 kcal/ mole, respectively. The heat of formation of the \cdot SiH₂ radical, 81 kcal/mole, agrees within experimental error with the value of 72 kcal/mole cited by Vedeneyev, et al.¹⁶ A comparison of the thermal properties of silylarsine and the $\cdot AsH_2$ radical with those reported earlier for silvlphosphine and the · PH₂ radical¹¹ shows that $D(H_2P-SiH_3)$ is more positive than $D(H_2As-$

(15) F. H. Field and J. L. Franklin, "Electron Impact Phenomena and the Properties of Gaseous Ions," Academic Press Inc., New York, N. Y., 1957. SiH₃), agreeing with the concept that the bond energy decreases in a chemical group as the atomic number increases. The data also show that the ionization potential of silylarsine equals that of silylphosphine and the ionization potentials of the radicals \cdot PH₂ and \cdot AsH₂ are equal. The heat of formation of the ions of arsine, like those of ammonia and phosphine, become more positive with the stepwise removal of hydrogen. In the series of ions formed from silylarsine, the loss of one hydrogen atom from the molecular ion yields the ion with the least positive heat of formation; then the heat of formation of the ions becomes more positive with each succeeding loss of hydrogen. The same trend can be noted for the ions produced from the related compound, methylamine.¹⁵

(16) V. I. Vedeneyev, L. V. Gurvich, V. N. Kondrat'yev, V. A. Mednedev, and Ye. L. Frankevich, "Bond Energies, Ionization Potentials and Electron Affinites," Edward Arnold Publishers Ltd., London, 1966, p 135; C. J. O'Brien and J. R. Perrine, "Kinetics, Equilibria and Performance of High Temperature Systems," London, 1960.

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A Proton Magnetic Resonance Study of Some Alkylalkoxysilanes

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Proton magnetic resonance data for several series of alkylalkoxysilanes, $R_{n-4}Si(OR)_n$, together with Si^{29} data from the literature, indicate that inductive electron withdrawal and $(p-d)\pi$ bonding of oxygen to silicon both contribute to electron densities in the molecules. The inductive effect *per alkoxy group* decreases as the number of alkoxy groups increases while the π -bonding effect *per alkoxy group* is either unchanged or diminished to only a slight extent as the number of alkoxy groups increases. Replacement of one alkyl groups in a tetraalkylsilane by an alkoxy group results in a *net* decrease but replacement of the second and remaining alkyl groups results in a *net* increase in electron density on silicon with corresponding changes in the electron densities on the alkyl and alkoxy protons. The importance of π -bonding effects in alkylalkoxy-silanes is further indicated by a comparison of the chemical shifts of the methoxy protons in trimethylmethoxysilane and *t*-butyl methyl ether. Data on some alkylchlorosilanes indicate that inductive effects in alkylchlorosilanes dominate over any π -bonding effects.

In the course of an investigation of alkoxy–alkoxy exchange² in some alkylalkoxyboranes by proton magnetic resonance methods, the chemical shifts of the α protons of the alkoxy groups were taken as evidence of extensive π bonding between oxygen and boron in alkylalkoxyboranes.

The present study of four series of alkylalkoxysilanes was initiated in order to determine whether evidence for π bonding between oxygen and silicon in alkylalkoxysilanes could be obtained.

Experimental Section

Reagents.—Methyltrimethoxy-, methyltriethoxy-, dimethyldiethoxy-, trimethylethoxy-, tetramethyl-, and ethyltriethoxysilane, and the alkylchlorosilanes, were obtained in pure grade from Anderson Laboratories, Inc., Weston, Mich. Tetraethoxysilane was supplied by E. H. Sargent & Co., Chicago, Ill., and tetraethylsilane was obtained from K & K Laboratories, Jamaica, N. Y. The remaining alkylalkoxysilanes were prepared by the method of Emeléus and Robinson.³ All compounds were purified by fractional distillation to give products with a boiling range of less than 0.2° .

Proton Magnetic Resonance Procedures.—Proton magnetic resonance spectra were obtained using a Varian Associates Model H-60, high-resolution, 60-Mc nmr spectrometer. Samples were sealed under dry nitrogen in 5×160 mm glass tubes. Chemical shifts were determined using the side-band technique with tetramethylsilane as an internal standard and were reproducible to 0.008 ppm.

Results

Intermolecular interactions were found to have no detectable influence on the chemical shifts of the protons in alkylalkoxysilanes. The spectra of the compounds were unchanged when concentrations in tetra-

⁽¹⁾ The Radiation Laboratory of the University of Notre Dame is operated under contract with the U. S. Atomic Energy Commission. This is AEC document COO-38-492.

⁽²⁾ P. A. McCusker and P. L. Pennartz, Abstracts, 140th National Meeting of the American Chemical Society, Chicago, Ill., Sept 1961, p 22-N.

⁽³⁾ H. J. Emeléus and S. R. Robinson, J. Chem. Soc., 1592 (1947).